

ABSTRACT

Disclosed are a semiconductor devices and method of fabricating the same. Anti-etch films are formed in the top corners of the device isolation film
5 using a material that has a different etch selectivity ratio from nitride or oxide and is not etched in an oxide gate pre-cleaning process. It is thus possible to prevent formation of a moat at the top corners of the device isolation film and the gate oxide film from being thinly formed, thereby improving reliability and electrical characteristics of the device.